ESD Protection Diodes

Micro-Packaged Diodes for ESD Protection

The ESD7451 is designed to protect voltage sensitive components that require ultra—low capacitance from ESD and transient voltage events. Excellent clamping capability, low capacitance, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its low capacitance, the part is well suited for use in high frequency designs such as USB 2.0 high speed and antenna line applications.



- Ultra-Low Capacitance (0.35 pF Max)
- Low Clamping Voltage
- Stand-off Voltage: 3.3 V
- Low Leakage
- Response Time is < 1 ns
- Low Dynamic Resistance $< 1 \Omega$
- Protection for the Following Standards: IEC 61000-4-2 (Level 4) & ISO 10605
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- RF Signal ESD Protection
- RF Switching, PA, and Antenna ESD Protection
- Near Field Communications

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Total Power Dissipation on FR–5 Board (Note 1) @ T _A = 25°C	P _D	250	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	400	°C/W
Junction and Storage Temperature Range	T_J , T_{stg}	-55 to +150	°C
Lead Solder Temperature – Maximum (10 Second Duration)	T_L	260	ů
IEC 61000–4–2 Contact IEC 61000–4–2 Air ISO 10605 150 pF/2 kΩ ISO 10605 330 pF/2 kΩ ISO 10605 330 pF/330 Ω	ESD	±25 ±25 ±30 ±30 ±20	kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. $FR-5 = 1.0 \times 0.75 \times 0.62$ in.

See Application Note AND8308/D for further description of survivability specs.

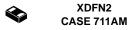


ON Semiconductor®

www.onsemi.com



MARKING DIAGRAM





E = Specific Device Code M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
ESD7451N2T5G	XDFN2 (Pb-Free)	8000 / Tape & Reel
SZESD7451N2T5G	XDFN2 (Pb-Free)	8000 / Tape & Reel

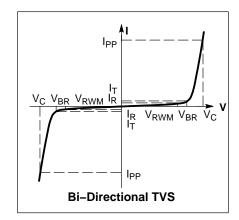
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Symbol	Parameter	
Ірр	Maximum Reverse Peak Pulse Current	
V _C	Clamping Voltage @ IPP	
V_{RWM}	Working Peak Reverse Voltage	
I _R	Maximum Reverse Leakage Current @ V _{RWM}	
V _{BR}	Breakdown Voltage @ I _T	
I _T	Test Current	

^{*}See Application Note AND8308/D for detailed explanations of datasheet parameters.

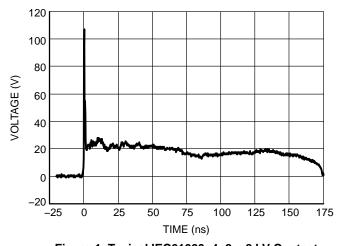


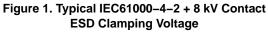
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V_{RWM}				3.3	V
Breakdown Voltage (Note 2)	V_{BR}	I _T = 1 mA	5.0	6.0	7.5	V
Reverse Leakage Current	I _R			< 1.0	50	nA
Clamping Voltage (Note 3)	V _C	I _{PP} = 1 A I _{PP} = 3 A			10 13	V
Clamping Voltage, ESD	V _C	Per IEC61000-4-2 Waveform	Se	e Figures 1	& 2	
Clamping Voltage, TLP	V _C	I _{PP} = ±8 A I _{PP} = ±16 A		13.5 18		V
Dynamic Resistance	R _{DYN}	TLP Pulse		0.55		Ω
Junction Capacitance	СЈ	$V_R = 0 \text{ V, } f = 1 \text{ MHz}$ $V_R = 0 \text{ V, } f = 1 \text{ GHz}$		0.25 0.22	0.35 0.35	pF

- Breakdown voltage is tested from pin 1 to 2 and pin 2 to 1.
 Non-repetitive current pulse at T_A = 25°C, per IEC61000-4-5 waveform shown in Figure 9.

TYPICAL CHARACTERISTICS





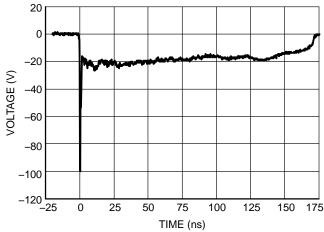


Figure 2. Typical IEC61000-4-2 - 8 kV Contact **ESD Clamping Voltage**

IEC 61000-4-2 Spec.

Level	Test Volt- age (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

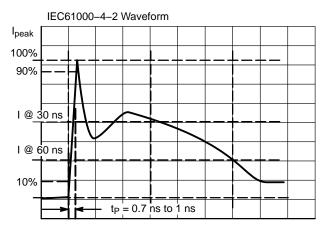


Figure 3. IEC61000-4-2 Spec

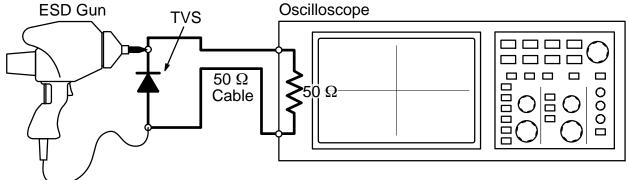


Figure 4. Diagram of ESD Test Setup

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000–4–2 waveform. Since the IEC61000–4–2 was written as a pass/fail spec for larger systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage

at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

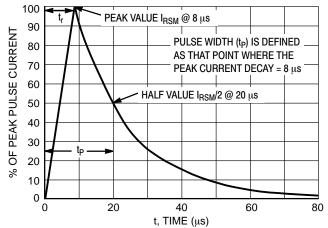


Figure 5. 8 X 20 µs Pulse Waveform

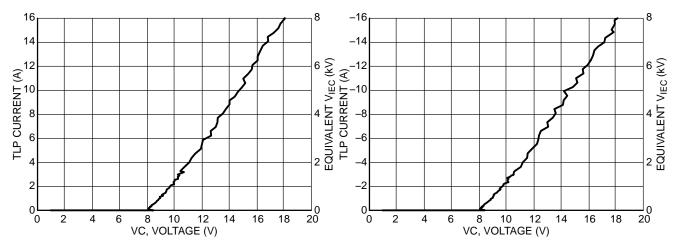


Figure 6. Typical Positive TLP IV Curve

Figure 7. Typical Negative TLP IV Curve

NOTE: TLP parameter: $Z_0 = 50 \Omega$, $t_p = 100 \text{ ns}$, $t_r = 300 \text{ ps}$, averaging window: $t_1 = 30 \text{ ns}$ to $t_2 = 60 \text{ ns}$.

Transmission Line Pulse (TLP) Measurement

Transmission Line Pulse (TLP) provides current versus voltage (I–V) curves in which each data point is obtained from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 8. TLP I–V curves of ESD protection devices accurately demonstrate the product's ESD capability because the 10s of amps current levels and under 100 ns time scale match those of an ESD event. This is illustrated in Figure 9 where an 8 kV IEC 61000–4–2 current waveform is compared with TLP current pulses at 8 A and 16 A. A TLP I–V curve shows the voltage at which the device turns on as well as how well the device clamps voltage over a range of current levels.

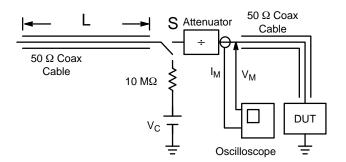


Figure 8. Simplified Schematic of a Typical TLP System

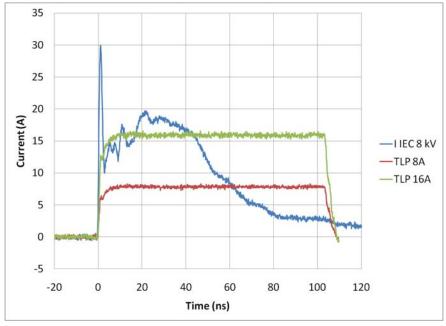
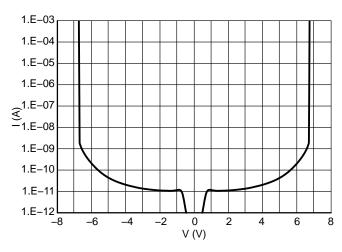


Figure 9. Comparison Between 8 kV IEC 61000-4-2 and 8 A and 16 A TLP Waveforms

TYPICAL CHARACTERISTICS



1.0 0.9 0.8 CAPACITANCE (pF) 0.7 0.6 0.5 0.4 0.3 0.2 0.1 -3 -2 0 2 3 VBias (V)

Figure 10. IV Characteristics

Figure 11. CV Characteristics

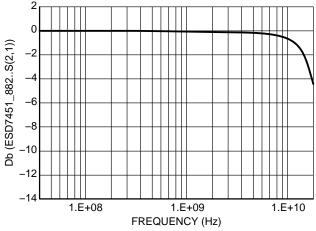


Figure 12. RF Insertion Loss

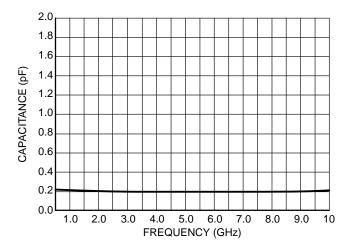
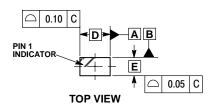
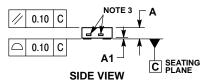


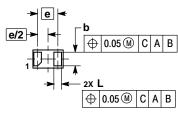
Figure 13. Capacitance over Frequency

PACKAGE DIMENSIONS

XDFN2 1.0x0.6, 0.65P (SOD-882)CASE 711AM ISSUE O







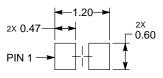
BOTTOM VIEW

NOTES:

- DIMENSIONING AND TOLERANCING PER
 ASME VALUE AND TOLERANCING PER
- ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
- B. EXPOSED COPPER ALLOWED AS SHOWN.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.34	0.44	
A1		0.05	
b	0.43	0.53	
D	1.00 BSC		
Е	0.60 BSC		
е	0.65 BSC		
L	0.20 0.30		

RECOMMENDED SOLDER FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center

Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative